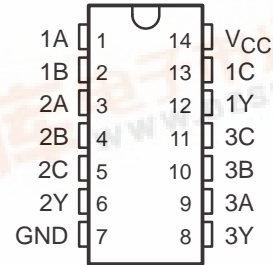


- **EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages**

**D, DGV, OR PW PACKAGE (TOP VIEW)**



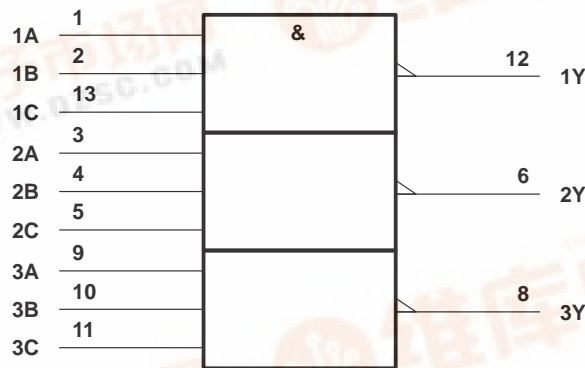
**description**

This triple 3-input positive-NAND gate is designed for 1.65-V to 3.6-V  $V_{CC}$  operation. The SN74ALVC10 performs the Boolean function  $Y = \overline{A \cdot B \cdot C}$  or  $Y = \overline{A} + \overline{B} + \overline{C}$  in positive logic. The SN74ALVC10 is characterized for operation from  $-40^{\circ}\text{C}$  to  $85^{\circ}\text{C}$ .

**FUNCTION TABLE (each gate)**

INPUTS			OUTPUT
A	B	C	Y
H	H	H	L
L	X	X	H
X	L	X	H
X	X	L	H

**logic symbol†**



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

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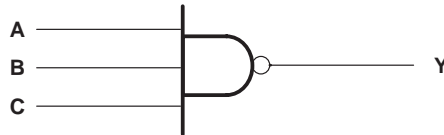
PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

# SN74ALVC10

## TRIPLE 3-INPUT POSITIVE-NAND GATE

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### logic diagram, each gate (positive logic)



### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage range, $V_{CC}$	−0.5 V to 4.6 V	
Input voltage range, $V_I$ (see Note 1)	−0.5 V to 4.6 V	
Output voltage range, $V_O$ (see Notes 1 and 2)	−0.5 V to $V_{CC} + 0.5$ V	
Input clamp current, $I_{IK}$ ( $V_I < 0$ )	−50 mA	
Output clamp current, $I_{OK}$ ( $V_O < 0$ )	−50 mA	
Continuous output current, $I_O$	±50 mA	
Continuous current through $V_{CC}$ or GND	±100 mA	
Package thermal impedance, $\theta_{JA}$ (see Note 3):	D package	127°C/W
	DGV package	182°C/W
	PW package	170°C/W
Storage temperature range, $T_{stg}$	−65°C to 150°C	

<sup>†</sup> Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. This value is limited to 4.6 V maximum.

3. The package thermal impedance is calculated in accordance with JESD 51.

### recommended operating conditions (see Note 4)

		MIN	MAX	UNIT
$V_{CC}$	Supply voltage	1.65	3.6	V
$V_{IH}$	High-level input voltage	$V_{CC} = 1.65$ V to $1.95$ V	$0.65 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to $2.7$ V	1.7	
		$V_{CC} = 2.7$ V to $3.6$ V	2	
$V_{IL}$	Low-level input voltage	$V_{CC} = 1.65$ V to $1.95$ V	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to $2.7$ V	0.7	
		$V_{CC} = 2.7$ V to $3.6$ V	0.8	
$V_I$	Input voltage	0	$V_{CC}$	V
$V_O$	Output voltage	0	$V_{CC}$	V
$I_{OH}$	High-level output current	$V_{CC} = 1.65$ V	−4	mA
		$V_{CC} = 2.3$ V	−12	
		$V_{CC} = 2.7$ V	−12	
		$V_{CC} = 3$ V	−24	
$I_{OL}$	Low-level output current	$V_{CC} = 1.65$ V	4	mA
		$V_{CC} = 2.3$ V	12	
		$V_{CC} = 2.7$ V	12	
		$V_{CC} = 3$ V	24	
$\Delta t/\Delta v$	Input transition rise or fall rate	0	5	ns/V
$T_A$	Operating free-air temperature	−40	85	°C

NOTE 4: All unused inputs of the device must be held at  $V_{CC}$  or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

# SN74ALVC10

## TRIPLE 3-INPUT POSITIVE-NAND GATE

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**electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)**

PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	MIN	TYP†	MAX	UNIT
V <sub>OH</sub>	I <sub>OH</sub> = -100 μA	1.65 V to 3.6 V	V <sub>CC</sub> -0.2			V
	I <sub>OH</sub> = -4 mA	1.65 V	1.2			
	I <sub>OH</sub> = -6 mA	2.3 V	2			
	I <sub>OH</sub> = -12 mA	2.3 V	1.7			
		2.7 V	2.2			
		3 V	2.4			
I <sub>OH</sub> = -24 mA	3 V	2				
V <sub>OL</sub>	I <sub>OL</sub> = 100 μA	1.65 V to 3.6 V			0.2	V
	I <sub>OL</sub> = 4 mA	1.65 V			0.45	
	I <sub>OL</sub> = 6 mA	2.3 V			0.4	
	I <sub>OL</sub> = 12 mA	2.3 V			0.7	
		2.7 V			0.4	
	I <sub>OL</sub> = 24 mA	3 V			0.55	
I <sub>I</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	3.6 V			±5	μA
I <sub>CC</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND, I <sub>O</sub> = 0	3.6 V			10	μA
ΔI <sub>CC</sub>	One input at V <sub>CC</sub> - 0.6 V, Other inputs at V <sub>CC</sub> or GND	3 V to 3.6 V			750	μA
C <sub>i</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V		4		pF

† All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C.

**switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)**

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1.8 V ± 0.15 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 2.7 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A, B, or C	Y	1.1	4.8	1	3	3.3		1	3	ns

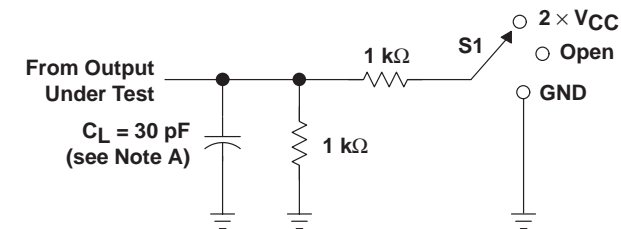
**operating characteristics, T<sub>A</sub> = 25°C**

PARAMETER	TEST CONDITIONS	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	UNIT
		TYP	TYP	TYP	
C <sub>pd</sub> Power dissipation capacitance per gate	C <sub>L</sub> = 0, f = 10 MHz	23	24	26	pF

# SN74ALVC10 TRIPLE 3-INPUT POSITIVE-NAND GATE

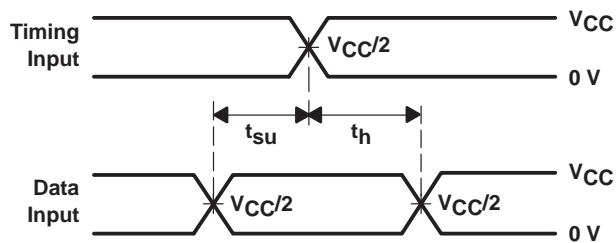
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## PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8\text{ V} \pm 0.15\text{ V}$

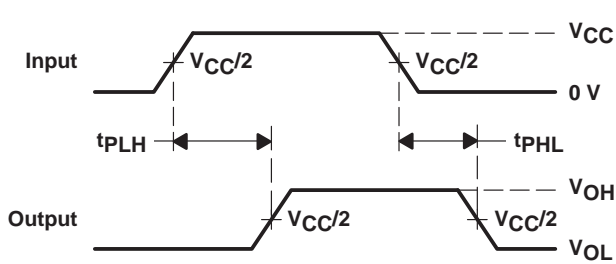


LOAD CIRCUIT

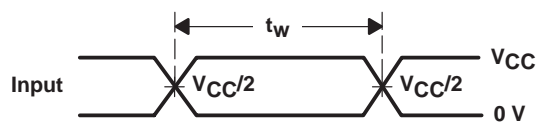
TEST	S1
$t_{pd}$	Open
$t_{PLZ}/t_{PZL}$	$2 \times V_{CC}$
$t_{PHZ}/t_{PZH}$	Open



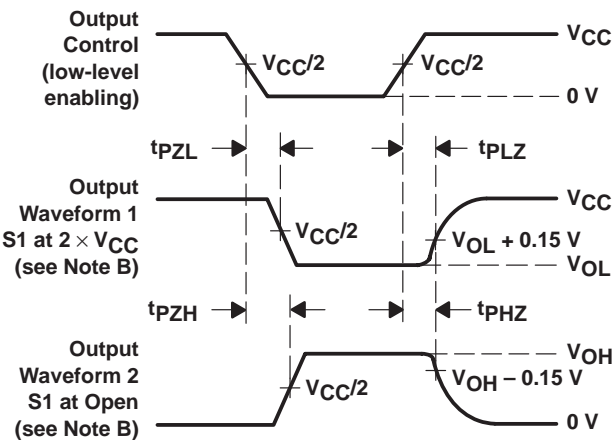
VOLTAGE WAVEFORMS  
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS  
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS  
PULSE DURATION



VOLTAGE WAVEFORMS  
ENABLE AND DISABLE TIMES

- NOTES:
- A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10\text{ MHz}$ ,  $Z_O = 50\ \Omega$ ,  $t_r \leq 2\text{ ns}$ ,  $t_f \leq 2\text{ ns}$ .
  - D. The outputs are measured one at a time with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

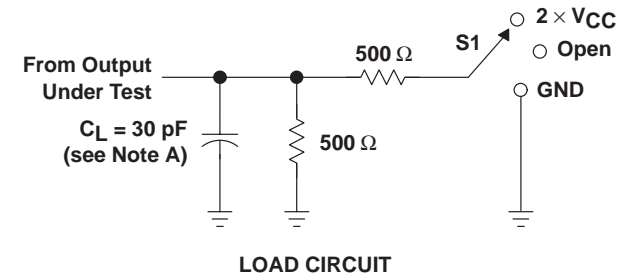
Figure 1. Load Circuit and Voltage Waveforms

# SN74ALVC10 TRIPLE 3-INPUT POSITIVE-NAND GATE

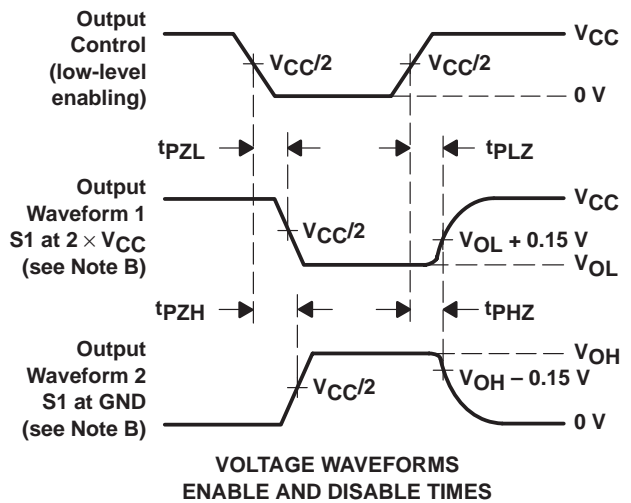
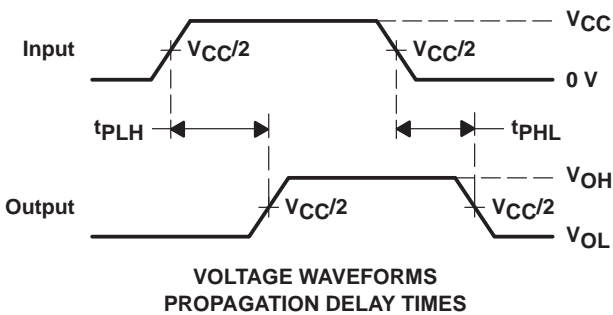
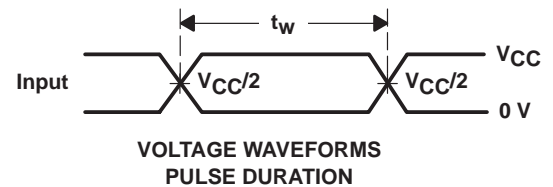
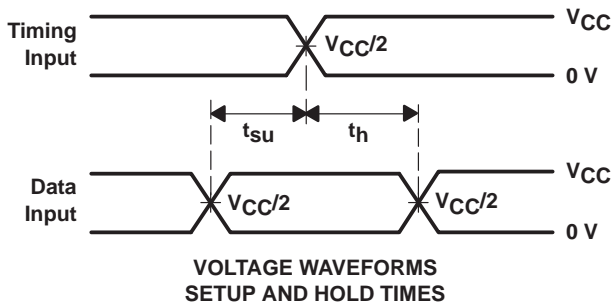
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## PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$



TEST	S1
$t_{pd}$	Open
$t_{PLZ}/t_{PZH}$	$2 \times V_{CC}$
$t_{PHZ}/t_{PHZ}$	GND



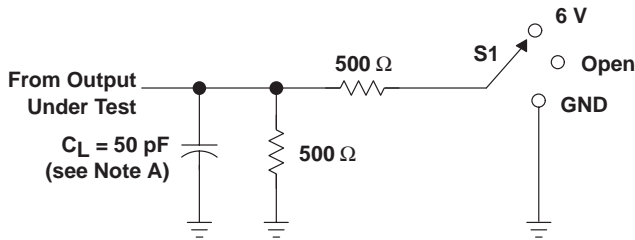
- NOTES:
- A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_r \leq 2 \text{ ns}$ ,  $t_f \leq 2 \text{ ns}$ .
  - D. The outputs are measured one at a time with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

**Figure 2. Load Circuit and Voltage Waveforms**

# SN74ALVC10 TRIPLE 3-INPUT POSITIVE-NAND GATE

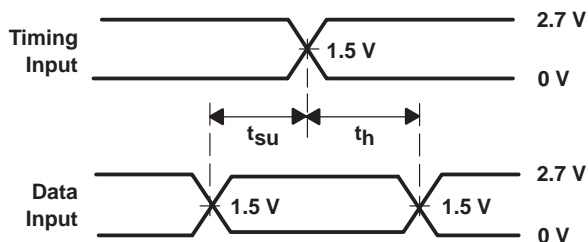
SCES106D – JULY 1997 – REVISED OCTOBER 1998

## PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.7\text{ V AND } 3.3\text{ V} \pm 0.3\text{ V}$

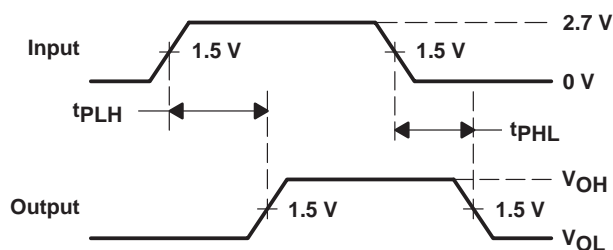


LOAD CIRCUIT

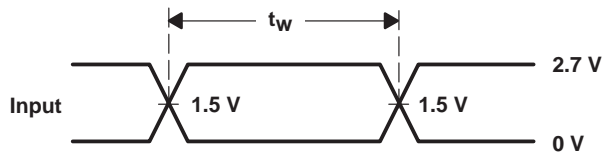
TEST	S1
$t_{pd}$	Open
$t_{PLZ}/t_{PZL}$	6 V
$t_{PHZ}/t_{PZH}$	GND



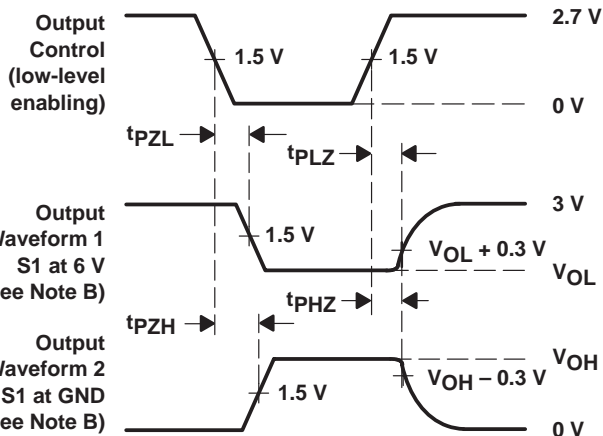
VOLTAGE WAVEFORMS  
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS  
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS  
PULSE DURATION



VOLTAGE WAVEFORMS  
ENABLE AND DISABLE TIMES

- NOTES: A.  $C_L$  includes probe and jig capacitance.  
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.  
 C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10\text{ MHz}$ ,  $Z_O = 50\ \Omega$ ,  $t_r \leq 2.5\text{ ns}$ ,  $t_f \leq 2.5\text{ ns}$ .  
 D. The outputs are measured one at a time with one transition per measurement.  
 E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .  
 F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .  
 G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

Figure 3. Load Circuit and Voltage Waveforms

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